

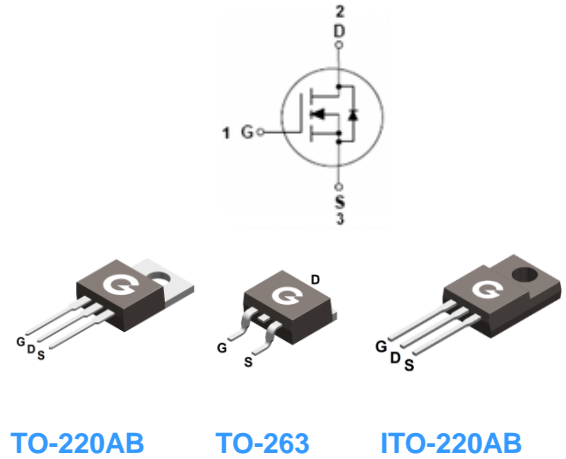
### Features

- Fast-recovery body diode
- Low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Improved dv/dt capability
- HBM: JESD22-A114-B: 1A

HF

### Mechanical Data

- Case: TO-220AB, TO-263, ITO-220AB
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matted-Tin plated; Solderable Per MIL-STD-202, Method 208



### Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL4K50	TO-220AB	50 pcs / Tube	4K50
BL4K50B	TO-263	50 pcs / Tube or 800 pcs / Tape & Reel	4K50B
BL4K50F	ITO-220AB	50 pcs / Tube	4K50F

### Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	500	V
Gate-to-Source Voltage	$V_{GSS}$	$\pm 30$	V
Continuous Drain Current ( $T_C = 25^\circ\text{C}$ )	$I_D$	4	A
Continuous Drain Current ( $T_C = 100^\circ\text{C}$ )		2.5	A
Pulsed Drain Current ( $t_p = 10\mu\text{s}$ , $T_C = 25^\circ\text{C}$ )	$I_{DM}$	16	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	200	mJ
Power Dissipation (TO-220AB, $T_C = 25^\circ\text{C}$ )	$P_D$	83	W
Power Dissipation (TO-263, $T_C = 25^\circ\text{C}$ )		83	W
Power Dissipation (ITO-220AB, $T_C = 25^\circ\text{C}$ )		31	W
Operating Junction Temperature Range	$T_J$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case (TO-220AB, TO-263)	R <sub>θJC</sub>	-	-	1.5	°C/W
Thermal Resistance Junction-to-Case (ITO-220AB)		-	2.9	4	°C/W
Thermal Resistance Junction-to-Air (TO-220AB, TO-263)	R <sub>θJA</sub>	-	-	50	°C/W
Thermal Resistance Junction-to-Air (ITO-220AB)		-	42	62.5	°C/W

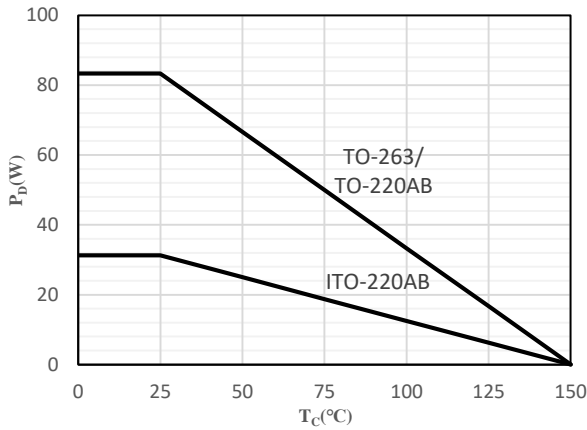
### Electrical Characteristics (@ T<sub>A</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
V <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	500	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V	-	-	1	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V	-	-	±100	nA
<b>On Characteristics</b>						
R <sub>DS(ON)</sub>	Drain-Source On-resistance *1	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2A	-	1.4	2.5	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0	2.8	4.0	V
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 0V, f = 1MHz	-	4.3	-	Ω
<b>Dynamic Characteristics</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz	-	650	-	pF
C <sub>OSS</sub>	Output Capacitance		-	58	-	
C <sub>RSS</sub>	Reverse Transfer Capacitance		-	2.5	-	
<b>Switching Characteristics</b>						
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> = 250V V <sub>GS</sub> = 15V I <sub>D</sub> = 4A R <sub>G</sub> = 10Ω	-	5	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	13	-	
t <sub>d(OFF)</sub>	Turn-Off Delay Time		-	20	-	
t <sub>f</sub>	Turn-Off Fall Time		-	37	-	
Q <sub>G</sub>	Total Gate-Charge	V <sub>DS</sub> = 400V V <sub>GS</sub> = 10V I <sub>D</sub> = 4A	-	13.1	-	nC
Q <sub>GS</sub>	Gate to Source Charge		-	3.3	-	
Q <sub>GD</sub>	Gate to Drain (Miller) Charge		-	5.3	-	
<b>Source-Drain Diode Characteristics</b>						
V <sub>SD</sub>	Diode Forward Voltage *1	I <sub>S</sub> = 4A, V <sub>GS</sub> = 0V	-	1	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>R</sub> = 400V, I <sub>S</sub> = 4A, di/dt = 100A/μs	-	80	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	96	-	nC

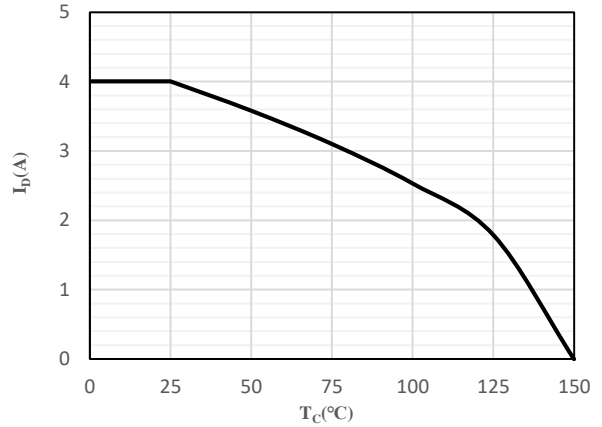
Notes:

- The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
- The E<sub>AS</sub> data shows Max. rating. The test condition is V<sub>DD</sub> = 100V, V<sub>GS</sub> = 15V, L = 50mH

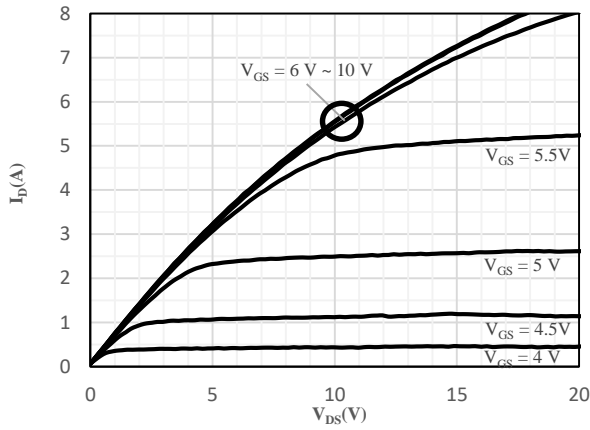
**Ratings and Characteristics Curves** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)



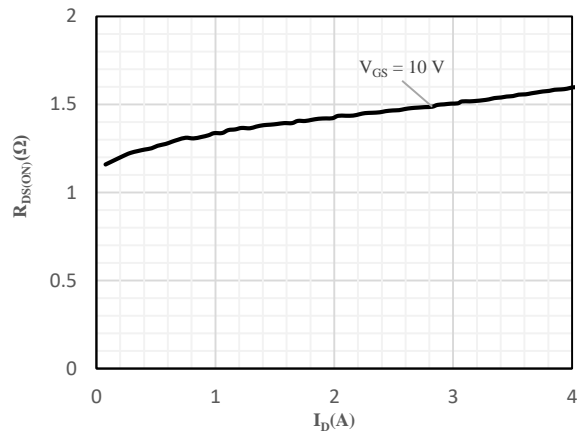
**Fig 1 Power Dissipation**



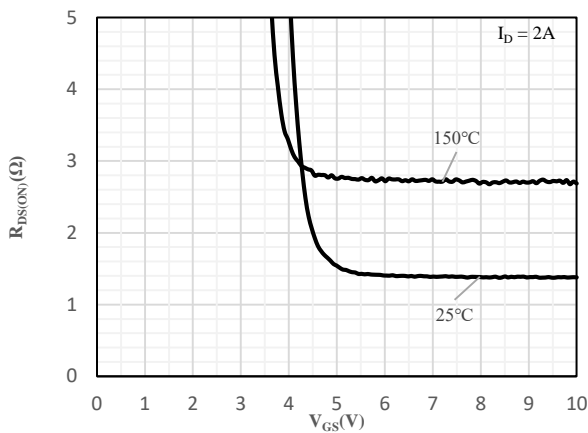
**Fig 2 Drain Current**



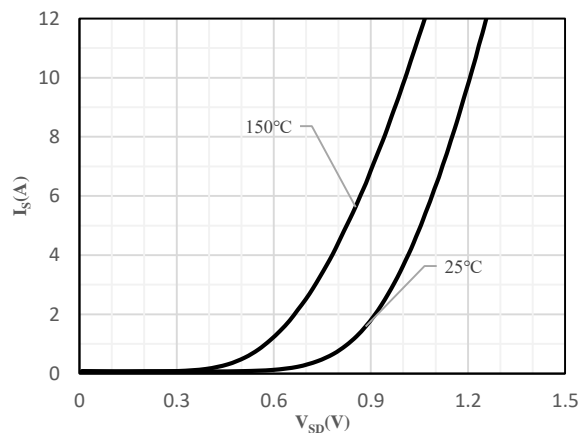
**Fig 3 Typical Output Characteristics**



**Fig 4 On-Resistance vs. Drain Current and Gate Voltage**



**Fig 5 On-Resistance vs. Gate-Source Voltage**



**Fig 6 Body-Diode Characteristics**

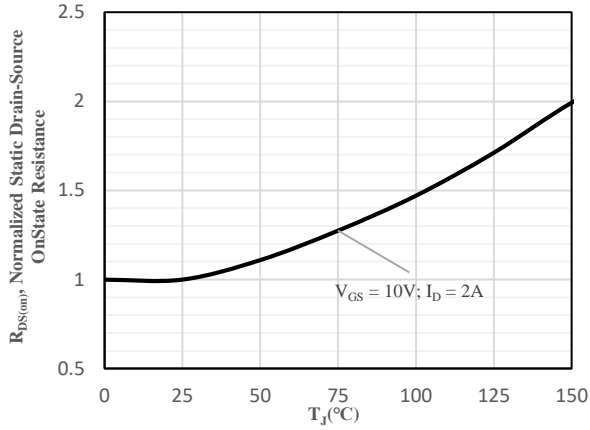


Fig 7 Normalized On-Resistance vs. Junction Temperature

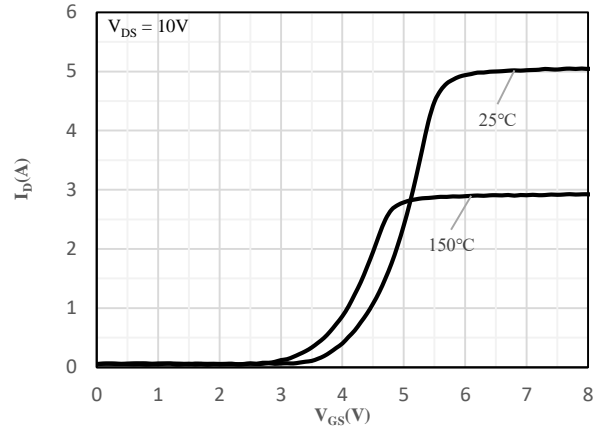


Fig 8 Transfer Characteristics

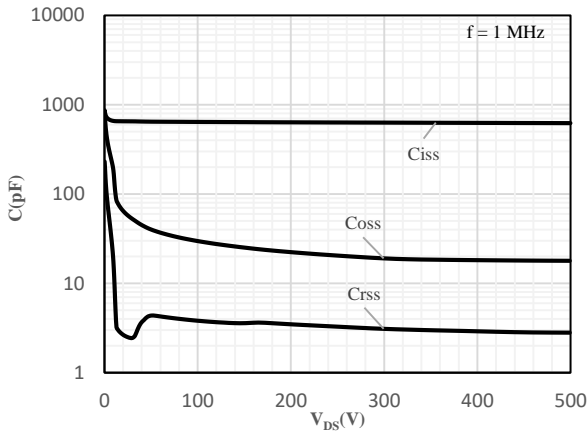


Fig 9 Capacitance Characteristics

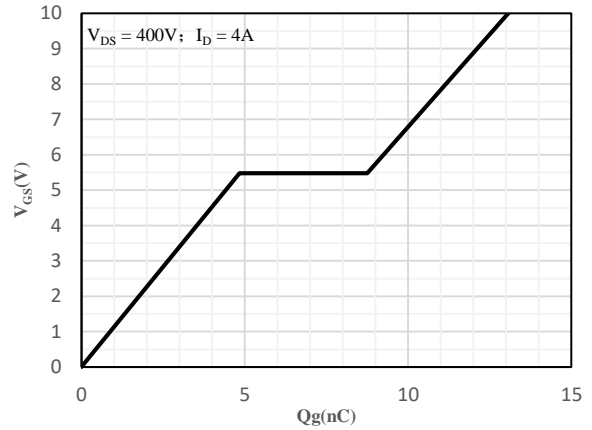


Fig 10 Gate-Charge Characteristics

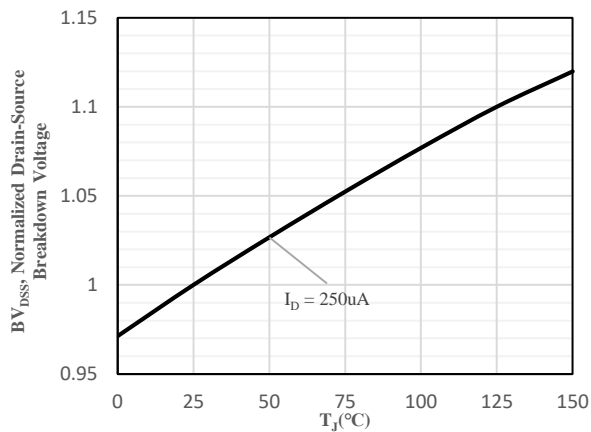


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

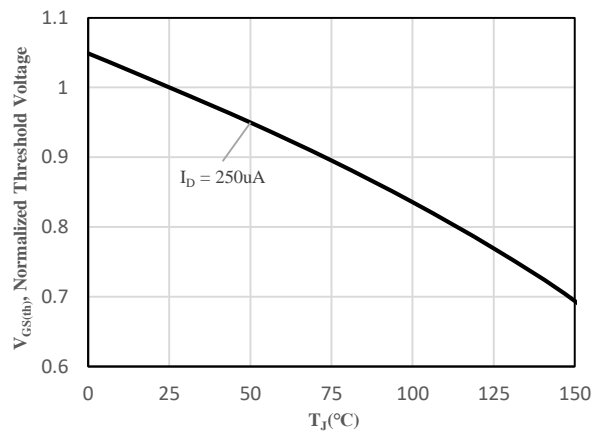
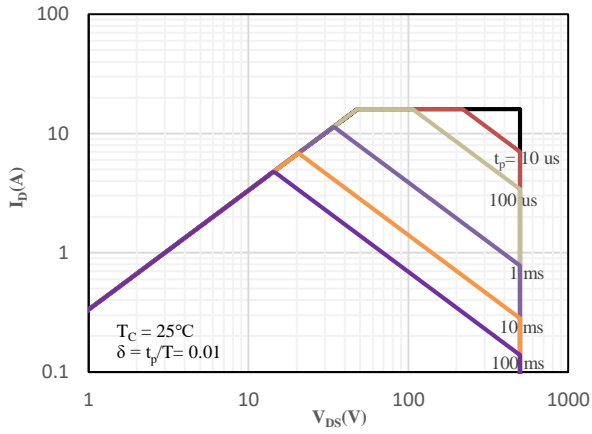
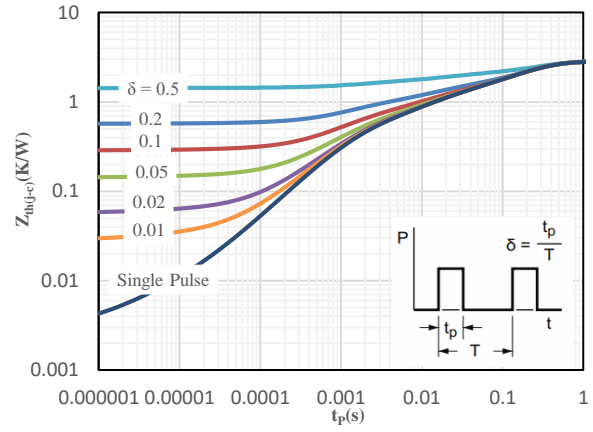


Fig 12 Normalized  $V_{GS(th)}$  vs. Junction Temperature

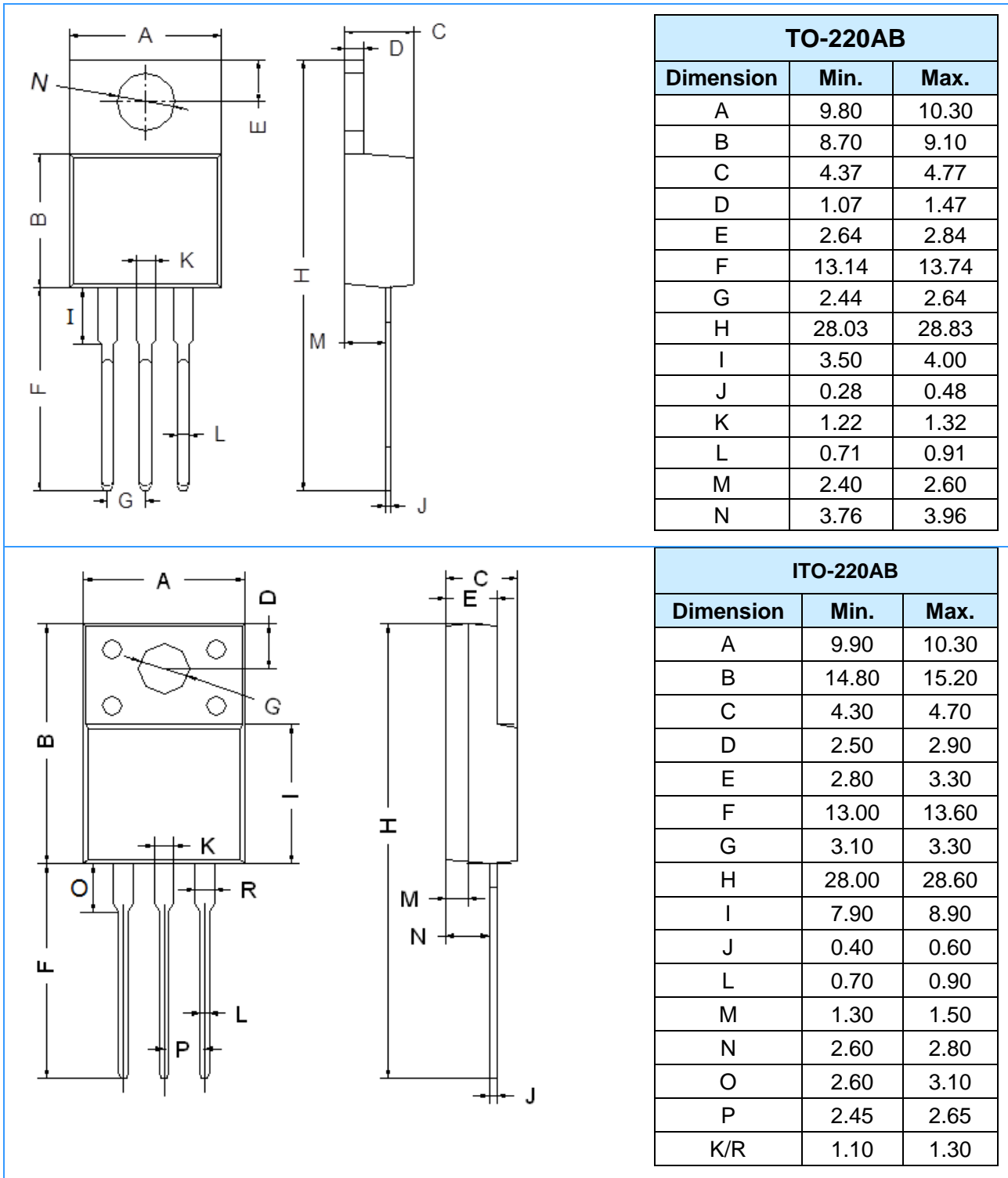


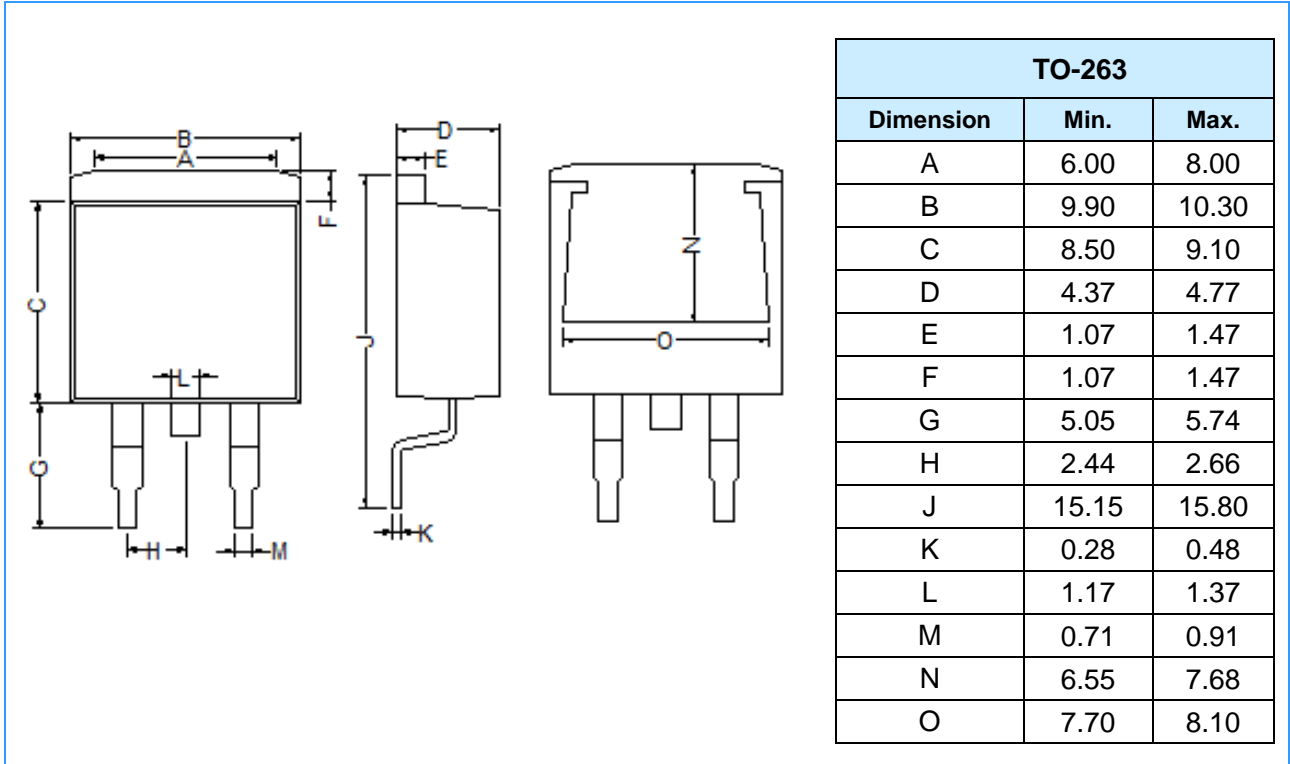
**Fig 13 Safe Operating Area (ITO-220AB)**



**Fig 14 Maximum transient thermal impedance (ITO-220AB)**

### Package Outline Dimensions (Unit: mm)





**Mounting Pad Layout** (Unit: mm)

